Oscar Martinez

List of Publications by Year
in descending order

81 papers	754 citations	623734 14 h-index	610901 24 g-index
81 all docs	81 docs citations	81 times ranked	1072 citing authors

#	Article	IF	Citations
1	Low-Cost Electronics for Online I-V Tracing at Photovoltaic Module Level: Development of Two Strategies and Comparison between Them. Electronics (Switzerland), 2021, 10, 671.	3.1	12
2	Daylight luminescence system for silicon solar panels based on a bias switching method. Energy Science and Engineering, 2020, 8, 3839-3853.	4.0	17
3	Effect of the Incorporation of Titanium on the Optical Properties of ZnO Thin Films: From Doping to Mixed Oxide Formation. Coatings, 2019, 9, 180.	2.6	9
4	MOVPE issues in the development of ordered GaInP metamorphic buffers for multijunction solar cells. , 2017, , .		1
5	Optical and structural characterisation of epitaxial nanoporous GaN grown by CVD. Nanotechnology, 2017, 28, 375701.	2.6	7
6	Polarization-Resolved Near-Field Spectroscopy of Localized States in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>m</mml:mi></mml:math> -Plane <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>In</mml:mi></mml:mrow><mml:mrow><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:mrow></mml:math> ma. Physical Review Applied, 2017, 7, .	3.8	16
7	Defect recognition by means of light and electron probe techniques for the characterization of mc-Si wafers and solar cells. Superlattices and Microstructures, 2016, 99, 45-53.	3.1	3
8	Doing physics experiments and learning with smartphones. , 2015, , .		6
9	Teaching and Learning Physics with Smartphones. Journal of Cases on Information Technology, 2015, 17, 31-50.	0.7	41
10	Epitaxial growth of (0001) oriented porous GaN layers by chemical vapour deposition. CrystEngComm, 2014, 16, 10255-10261.	2.6	9
11	Fully Porous GaN pâ€“n Junction Diodes Fabricated by Chemical Vapor Deposition. ACS Applied Materials & Interfaces, 2014, 6, 17954-17964.	8.0	25
12	Residual Strain and Electrical Activity of Defects in Multicrystalline Silicon Solar Cells. Acta Physica Polonica A, 2014, 125, 1013-1016.	0.5	3
13	Modification of the optical and structural properties of ZnO nanowires by low-energy Ar+ ion sputtering. Nanoscale Research Letters, 2013, 8, 162.	5.7	13
14	Study of a tabernacle with a remarkable architectural structure: In situ examination using Raman spectroscopy. Journal of Raman Spectroscopy, 2013, 44, 1156-1162.	2.5	6
15	Influence of metal organic chemical vapour deposition growth conditions on vibrational and luminescent properties of ZnO nanorods. Journal of Applied Physics, 2013, 113, .	2.5	11
16	Growth of CdS and CdTe films by close space vapour sublimation by using SiC resistive elements. CrystEngComm, 2013, 15, 2314.	2.6	19
17	Non-radiative recombination centres in catalyst-free ZnO nanorods grown by atmospheric-metal organic chemical vapour deposition. Journal Physics D: Applied Physics, 2013, 46, 235302.	2.8	101
18	Ion irradiation induced formation of CdO microcrystals on CdTe surfaces. Materials Letters, 2013, 92, 397-400.	2.6	7

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19	Cathodoluminescence Study of Ammonothermal GaN Crystals. Materials Science Forum, 2012, 725, 63-66.	0.3	2
20	Raman Spectroscopy Analysis of a Playing Card from the 18th Century. Spectroscopy Letters, 2012, 45, 114-117.	1.0	1
21	Characterization of CdZnTe after argon ion beam bombardment. Journal of Alloys and Compounds, 2012, 543, 233-238.	5.5	13
22	AFM morphological characterization and Raman study of germanium grown on (111)GaAs. Surface Science, 2012, 606, 808-812.	1.9	2
23	Electrical and optical characterization of extended defects in silicon mono-cast material. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 2158-2163.	0.8	7
24	Identification of Explosive Substances Through Improved Signals Obtained by a Portable Raman Spectrometer. Spectroscopy Letters, 2012, 45, 413-419.	1.0	11
25	Spectrally resolved cathodoluminescence imaging study of periodic [001]/[00-1] GaAs structures for nonlinear optical conversion. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1674-1676.	0.8	1
26	Luminescence studies of isolated ZnO nanowires grown by the vapourâ€liquidâ€solid method. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1537-1539.	0.8	2
27	Cathodoluminescence study of eâ€irradiated and plastically deformed ZnO crystals. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1580-1582.	0.8	2
28	Raman scattering by the E2h and A1(LO) phonons of InxGa1â^'xN epilayers (0.25 < x < 0.75) grown by molecular beam epitaxy. Journal of Applied Physics, 2012, 111, 063502.	2.5	25
29	Influence of different surface treatments on multicrystalline silicon wafers for defect characterization by LBIC. Journal of Materials Science, 2012, 47, 5470-5476.	3.7	3
30	Nanodot and nanocrystal pattern formation and luminescent properties of BiB3O6 glasses after moderate energy ion beam sputtering. Nuclear Instruments & Methods in Physics Research B, 2012, 272, 466-470.	1.4	1
31	Growth of ZnO nanowires through thermal oxidation of metallic zinc films on CdTe substrates. Journal of Alloys and Compounds, 2011, 509, 5400-5407.	5.5	15
32	Si and Si_xGe_{1â€x} NWs studied by Raman spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1307-1310.	0.8	2
33	Cathodoluminescence Study of Orientation-Patterned GaAs Crystals for Nonlinear Optics. Journal of Electronic Materials, 2010, 39, 805-810.	2.2	4
34	A Spectrum Image Cathodoluminescence Study of Dislocations in Si-Doped Liquid-Encapsulated Czochralski GaAs Crystals. Journal of Electronic Materials, 2010, 39, 781-786.	2.2	2
35	LBIC and Reflectance Mapping of Multicrystalline Si Solar Cells. Journal of Electronic Materials, 2010, 39, 663-670.	2.2	26
36	Effect on Ordering of the Growth of GaInP Layers on (111)-GaAs Faces. Journal of Electronic Materials, 2010, 39, 671-676.	2.2	3

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37	Raman spectroscopy analysis of ecclesiastical bulls inks and gilded copper enamels. Physics Procedia, 2010, 8, 10-13.	1.2	0
38	Raman spectroscopy study of group IV semiconductor nanowires. Physics Procedia, 2010, 8, 78-83.	1.2	1
39	Factors affecting the luminescence emission of InGaN multiâ€quantum wells grown on (0001) sapphire substrates by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 68-71.	0.8	1
40	Light Beam Induced Current Mapping of mc-Si Solar Cells: Influence of Grain Boundaries and Intragrain Defects. Materials Research Society Symposia Proceedings, 2010, 1268, 1.	0.1	2
41	Effect of low energy ion irradiation on CdTe crystals: Luminescence enhancement. Journal of Applied Physics, 2010, 108, 123513.	2.5	5
42	InGaP Layers Grown on Different GaAs Surfaces for High Efficiency Solar Cells. Materials Research Society Symposia Proceedings, 2009, 1167, 4.	0.1	2
43	Strain Evaluation in SiC MEMS Test Structures. ECS Transactions, 2009, 25, 1031-1037.	0.5	0
44	Continuous and Localized Mn Implantation of ZnO. Nanoscale Research Letters, 2009, 4, 878-887.	5.7	17
45	Properties of orientation-patterned GaAs crystals studied by cathodoluminescence spectroscopy. Superlattices and Microstructures, 2009, 45, 337-342.	3.1	2
46	Spectral image cathodoluminescence, photoluminescence and Raman study of GaAs layers grown on Si substrates. Superlattices and Microstructures, 2009, 45, 214-221.	3.1	0
47	Luminescence effects of ion-beam bombardment of CdTe surfaces. Journal of Luminescence, 2009, 129, 941-944.	3.1	7
48	New method for fabricating ZnO nanowires deposited onto CdTe substrates. Journal of Crystal Growth, 2009, 312, 64-67.	1.5	6
49	Growth and Characterization of 3C-SiC Films for Micro Electro Mechanical Systems (MEMS) Applications. Crystal Growth and Design, 2009, 9, 4852-4859.	3.0	36
50	Formation of ZnO and Zn1âˆ’xCdxO films on CdTe/CdZnTe single crystals. Applied Surface Science, 2008, 254, 5403-5407.	6.1	8
51	Nanostructures with Group IV Nanocrystals Obtained by LPCVD and Thermal Annealing of SiGeO Layers. Materials Research Society Symposia Proceedings, 2008, 1066, 1.	0.1	0
52	Raman Spectroscopy of Group IV Nanostructured Semiconductors: Influence of Size and Temperature. Materials Research Society Symposia Proceedings, 2008, 1145, 1.	0.1	0
53	A Study of Conformal GaAs on Si Layers by Micro-Raman and Spectral Imaging Cathodoluminescence. Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	0
54	Cathodoluminescence Study of Orientation Patterned GaAs Crystals for Nonlinear Optical Frequency Conversion by Quasi-Phase-Matching. Materials Research Society Symposia Proceedings, 2008, 1108, 1.	0.1	0

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55	Raman scattering and cathodoluminescence characterization of near lattice-matched InxAl1â^'xN epilayers. Semiconductor Science and Technology, 2008, 23, 105002.	2.0	1
56	Hexagonal CdTe-Like Rods Prompted from Bi2Te3Droplets. Journal of Physical Chemistry C, 2007, 111, 5588-5591.	3.1	12
57	Raman and luminescence probes for the study of compound semiconductors. Thin Solid Films, 2007, 515, 4412-4418.	1.8	1
58	Structural and optical characterization of pure ZnO films synthesised by thermal annealing on GaSb single crystals. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 1527-1531.	0.8	4
59	Luminescence of pure and doped ZnO films synthesised by thermal annealing on GaSb single crystals. Superlattices and Microstructures, 2007, 42, 145-151.	3.1	13
60	Growth and properties of CdTe:Bi-doped crystals. Journal of Crystal Growth, 2006, 291, 416-423.	1.5	28
61	Simulation and characterization of CdTe:Bi crystals grown by the Markov method. Journal of Crystal Growth, 2005, 275, e471-e477.	1.5	16
62	Cathodoluminescence study of Si complex formation in self-doped and intentionally Si-doped GaAs conformal layers. Journal of Physics Condensed Matter, 2004, 16, S99-S106.	1.8	0
63	Optical and structural characterization of self-organized stacked GaN/AlN quantum dots. Journal of Physics Condensed Matter, 2004, 16, S115-S126.	1.8	23
64	Compositional and optical uniformity of InGaN layers deposited on (0001) sapphire by metalâ€“organic vapour phase epitaxy. Semiconductor Science and Technology, 2004, 19, 147-151.	2.0	14
65	Optical and morphological characteristics of LP MOVPE grown lattice matched GaInP/GaAs heterostructures. Physica Status Solidi A, 2003, 195, 50-55.	1.7	6
66	Cathodoluminescence and micro-Raman characterisation of GaN/AlN QDs grown on Si (111). Physica Status Solidi A, 2003, 195, 26-31.	1.7	7
67	Temperature dependence of the Raman shift in GaAs conformal layers grown by hydride vapor phase epitaxy. Journal of Applied Physics, 2002, 91, 5045-5050.	2.5	17
68	Optical and structural characterization of GaN/AlN quantum dots grown on Si(111). Journal of Physics Condensed Matter, 2002, 14, 13329-13336.	1.8	9
69	Optical Characterization of GaAs/Si Layers Grown by the Conformal Method (Confined Lateral) Tj ETQq1 1 0.784314 rgBT /Overlock 10	2.6	6
70	Optical and structural characterization of LP MOVPE grown lattice matched InGaP/GaAs heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 123-127.	3.5	2
71	Study of defects in conformal GaAs/Si layers by optical techniques and photoetching. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 70-74.	3.5	1
72	Properties of AlGaAs layers grown on Si by the conformal method. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 91-95.	3.5	0

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73	Selective doping of conformal GaAs layers grown by hydride vapour phase epitaxy on Si substrates studied by spatially resolved optical techniques. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 197-201.	3.5	1
74	Evidence for surface initiated solidification in Ge films upon picosecond laser pulse irradiation. Journal of Applied Physics, 2001, 89, 3642-3649.	2.5	14
75	Self-doping near the seed/layer interface in conformal GaAs layers grown on Si. Applied Physics Letters, 2001, 79, 1270-1272.	3.3	6
76	Characterization of GaAs conformal layers grown by hydride vapour phase epitaxy on Si substrates by microphotoluminescence cathodoluminescence and microRaman. Journal of Crystal Growth, 2000, 210, 198-202.	1.5	4
77	Analysis of grain orientation and intergrain properties by micro-Raman spectroscopy in YBa2Cu3O7âˆ’x thin films. Journal of Materials Research, 2000, 15, 1069-1075.	2.6	3
78	A microRaman study of the structural properties of PLD high Tc superconducting thin films. Physica C: Superconductivity and Its Applications, 1996, 270, 144-154.	1.2	13
79	Oxygen content of YBaCuO thin films. Physica C: Superconductivity and Its Applications, 1996, 256, 291-297.	1.2	37
80	Combined EL and LBIC Study of the Electrical Activity of Defects in Solar Cells Based on Innovative Wafers Grown by Casting Methods. Materials Science Forum, 0, 725, 137-140.	0.3	0
81	Structural Characterization of 3C-SiC Grown Using Methyltrichlorosilane. Materials Science Forum, 0, 740-742, 291-294.	0.3	1